WHAT IS CLAIMED IS

1. A method for manufacturing a semiconductor package, the method comprising the steps of:

attaching a bottom surface of a semiconductor wafer to a first supporting member;

forming a through hole in the semiconductor wafer;

separating the semiconductor wafer from the first supporting member;

forming an insulating layer on at least the bottom surface of the semiconductor wafer and the inner wall of the through hole;

forming a conducting layer underneath the semiconductor wafer, the conducting layer spanning at least the bottom of the through hole; and

forming a conductive member in the through hole and in electrical contact with the conducting layer.

2. The method as claimed in claim 1, further comprising a step of thin-filming the semiconductor wafer.

3. The method as claimed in claim 1, wherein the conductive member is formed by plating.

4. The method as claimed in claim 1, further comprising a step of removing at least a portion of the conducting layer.

5. The method as claimed in claim 4, wherein a portion of the conducting layer beneath the conducting member is left remaining in the step of removing at least a portion of the conducting layer.

6. The method as claimed in claim 1, wherein the conducting layer is a tape member.

7. The method as claimed in claim 1, wherein the through hole is formed by etching.

8. The method as claimed in claim 1, wherein the insulating layer is formed on the surface of the semiconductor wafer by forming an inorganic insulating layer on the surface of the semiconductor wafer, and forming an organic insulating layer on the surface of the inorganic insulating layer.

9. The method as claimed in claim 1, wherein a barrier layer is formed on the insulating layer subsequent to the step of forming the insulating layer.

10. A method for manufacturing a semiconductor package, the method comprising the steps of:

attaching a bottom surface of a semiconductor wafer to a first supporting member;

forming a through hole in the semiconductor wafer;

separating the semiconductor wafer from the first supporting member;

forming an insulating layer on at least the bottom surface of the semiconductor wafer and the inner wall of the through hole;

attaching the semiconductor wafer to a top surface of a second supporting member, the top surface spanning at least the bottom of the through hole;

forming a conducting layer on at least the bottom of the through hole; and

forming a conductive member in the through hole.

11. The method as claimed in claim 10, further comprising a step of thin-filming the semiconductor wafer.

12. The method as claimed in claim 10, wherein the conductive member is formed by plating.

13. The method as claimed in claim 10, wherein the through hole is formed by etching.

14. The method as claimed in claim 10, wherein the insulating layer is formed on the

surface of the semiconductor wafer by forming an inorganic insulating layer on the surface of the semiconductor wafer, and forming an organic insulating layer on the surface of the inorganic insulating layer.

15. The method as claimed in claim 10, wherein a barrier layer is formed on the insulating layer subsequent to the step of forming the insulating layer.